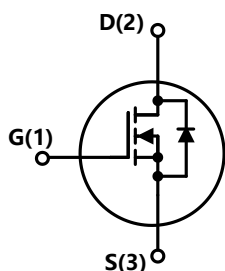
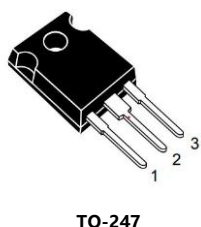


N-channel 650V 34mΩ (Typ) Power MOSFET

1 FEATURES

- 650V break down voltage
- Ultra-low R_{DS-ON} & FOM
- Fast switching on/off
- Ultra-fast body diode integrated



2 APPLICATIONS

- Server power
- Telecom power
- EV charger
- Motor driver

3 ORDERING INFORMATION

TYPE	MARKING	PACKAGE
GBS65041CTOB	65041	TO-247

4 DISCRIPTION

The 650V high voltage Super Junction MOSFET achieves ultra-low ON-resistance and gate charge. Thanks to excellent balance between switching performance and conduction performance, the GBS65041C provides very high efficiency in various switch topology.

The Ultra-fast recovery body diode makes the GBS65041C suitable for high switching frequency application and supports high power density application. The GBS65041C is available in TO-247 package.

5 KEY PERFORMANCE PARAMETERS

PARAMETER	VALUE	UNIT
$V_{DS} @ T_{j_max}$	700	V
$R_{DS-ON} \text{ max } @ V_{GS}=10V$	40	mΩ
$Q_g \text{ (Typ)}$	130	nC
$I_{D-pulse}$	216	A
$E_{oss}@400V$	18	μJ
Body diode recovery time	170	ns



6 SPECIFICATIONS

6.1 ABSOLUTE MAXIMUM RATINGS

T_J=25°C operating free-air temperature unless otherwise noted

SYMBOL	PARAMETER	TEST CONDITION	VALUE	UNIT
V _{DS}	Drain-source voltage		650	V
I _D	Continuous drain current	T _C =25°C	54	A
		T _C =100°C	34	
I _{D-pulse}	Pulsed drain current		216	A
V _{GS}	Gate-source voltage		±30	V
E _{AS}	Single pulsed avalanche energy	I _D =6A, V _{DD} =50V	200	mJ
E _{AR}	Repetitive avalanche energy	I _D =6A, V _{DD} =50V	1	mJ
I _{AS}	Single pulsed avalanche current		6	A
P _D	Power dissipation		450	W
dv/dt	MOSFET dv/dt ruggedness	V _{DS} =0~400V	60	V/ns
I _S	Continuous diode forward current		54	A
I _{S-pulse}	Diode pulsed current		216	A
dv/dt	Reverse diode dv/dt	V _{DS} =0~400V, I _{SD} <25A	50	V/ns
T _{stg}	Storage temperature		-55 ~ 150	°C

6.2 THERMAL INFORMATION

SYMBOL	PARAMETER	VALUE	UNIT
R _{θJC} max.	Max. Thermal resistance, junction - case	0.54	°C/W
R _{θJA} max.	Max. Thermal resistance, junction - ambient	62	°C/W
T _{sold}	Soldering temperature	260	°C

6.3 ELECTRICAL CHARACTERISTICS

T_J=25°C operating free-air temperature unless otherwise noted

SYMBOL	PARAMETER	TEST CONDITION	MIN	TYP	MAX	UNIT
STATIC CHARACTERISTICS						
V _{(BR)DSS}	Drain-source breakdown voltage	V _{GS} =0V, I _D =10mA	650			V
		V _{GS} =0V, I _D =10mA, T _J =150°C	700			



SYMBOL	PARAMETER	TEST CONDITION	MIN	TYP	MAX	UNIT
V _{(GS)th}	Gate threshold voltage	V _{DS} =V _{GS} , I _D =1mA	3.4	4	4.6	V
R _{DS-ON}	Drain-source on state resistance	V _{GS} =10V, I _D =25A		34	40	mΩ
		V _{GS} =10V, I _D =25A, T _j =125°C		74		
I _{GSS}	Gate-source leakage current	V _{GS} =30V, V _{DS} =0V			100	nA
I _{DSS}	Drain-source leakage current	V _{GS} =0V, V _{DS} =650V			1	uA
		V _{GS} =0V, V _{DS} =650V, T _j =125°C			500	
DYNAMIC CHARACTERISTICS						
C _{iss}	Input capacitance	V _{GS} =0V		6300		pF
C _{oss}	Output capacitance	V _{DS} =400V, f=250KHz		95		pF
C _{rss}	Reverse transfer capacitance			4		pF
C _{o(er)}	Effective output capacitance, energy related	V _{GS} = 0V, V _{DS} = 0V~400V		225		pF
C _{o(tr)}	Effective output capacitance, time related			2435		pF
t _{d(on)}	Turn-on delay time	V _{GS} =14V, V _{DS} =400V, R _G =3Ω		50		ns
t _r	Rise time			11		ns
t _{d(off)}	Turn-off delay time			110		ns
t _f	Fall time			6		ns
GATE CHARGE CHARACTERISTICS						
Q _g	Gate charge total	V _{DS} =400V, I _D =25A V _{GS} =0~10V		130		nC
Q _{gd}	Gate to drain charge			48		nC
Q _{gs}	Gate to source charge			38		nC
V _{plateau}	Gate plateau voltage			6.2		V
BODY DIODE CHARACTERISTICS						
V _{SD}	Diode forward voltage	V _{GS} =0V, I _F =25A, T _j =25°C			1.3	V
t _{rr}	Reverse recovery time	V _{DS} =400V, I _F =25A		170		ns
Q _{rr}	Reverse recovery charge			1.2		μC



SYMBOL	PARAMETER	TEST CONDITION	MIN	TYP	MAX	UNIT
I_{rr}	Peak reverse recovery current	$di_F/dt=100A/\mu s$		14.2		A

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7 Electrical Characteristic Diagram

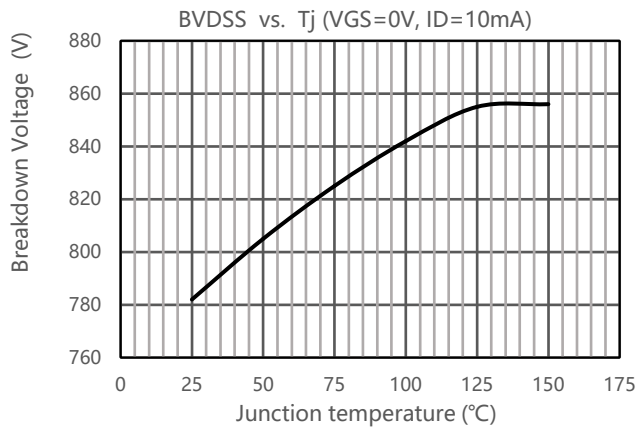


Figure 1. Drain-source Breakdown Voltage

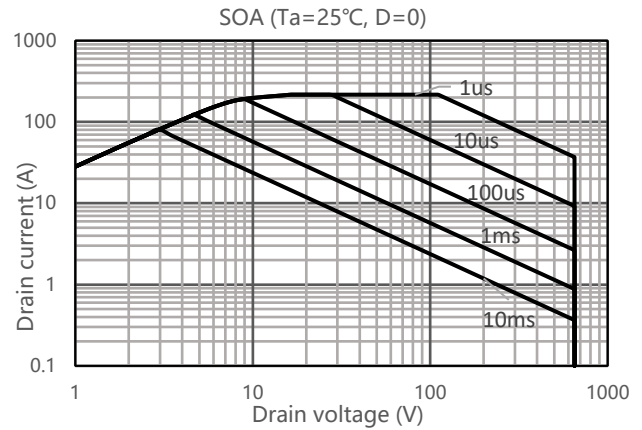


Figure 2. Safety Operating Area

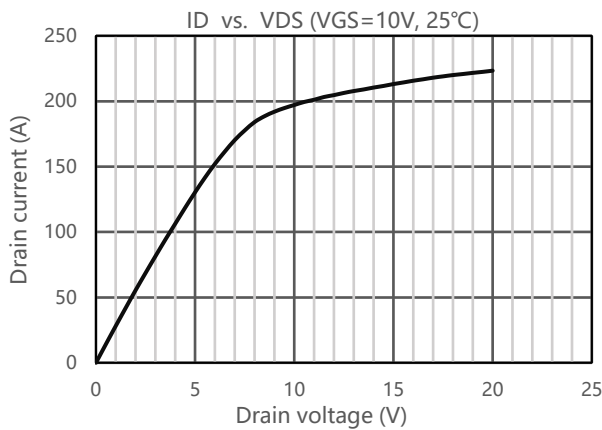


Figure 3. Typ. Output Characteristics

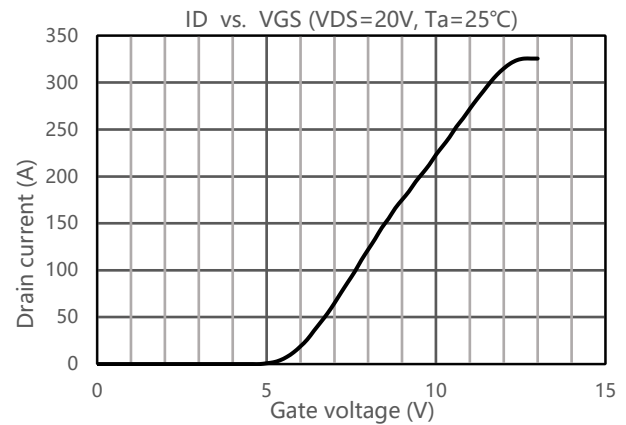


Figure 4. Typ. Transfer Characteristics

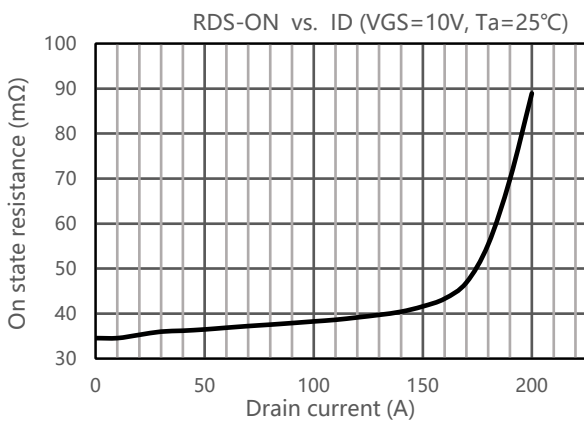


Figure 5. Typ. Drain Source On-state Resistance

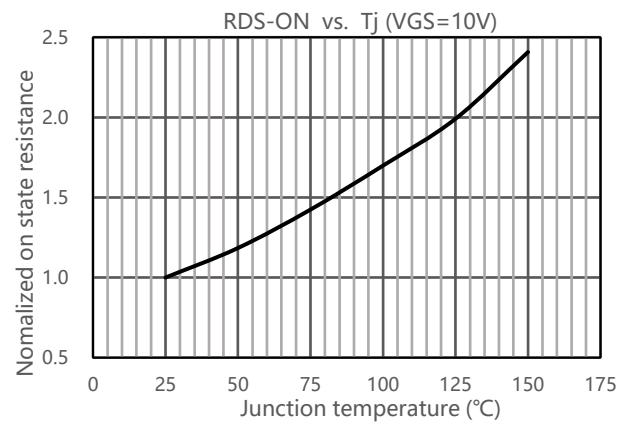


Figure 6. R_{DS-ON} vs. T_j

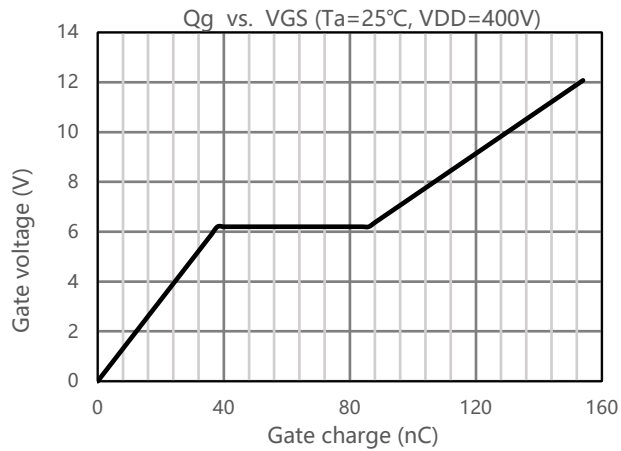


Figure 7. Typ. Gate Charge

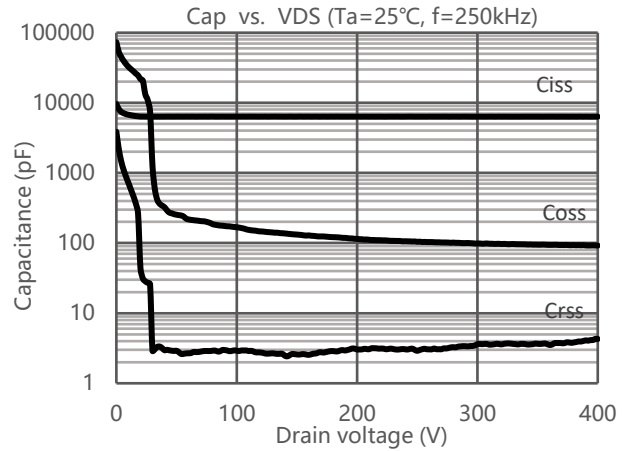


Figure 8. Typ. Capacitance

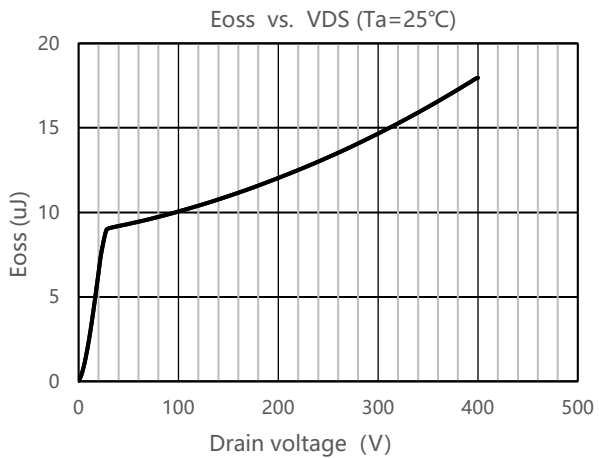


Figure 9. Typ. Coss Stored Energy

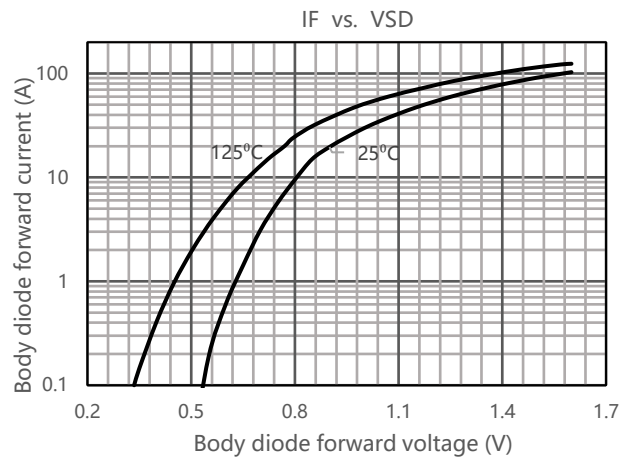


Figure 10. Body diode forward characteristics

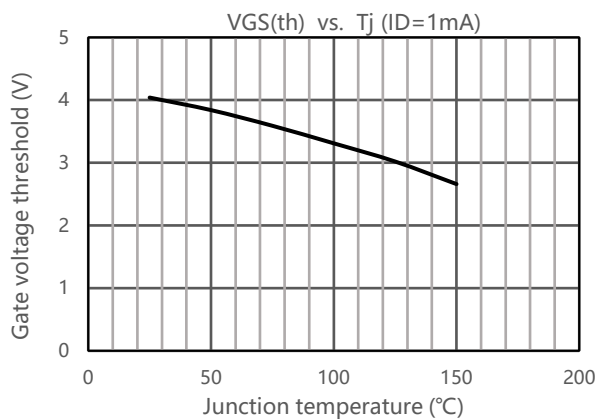


Figure 11. Threshold Voltage vs. Tj

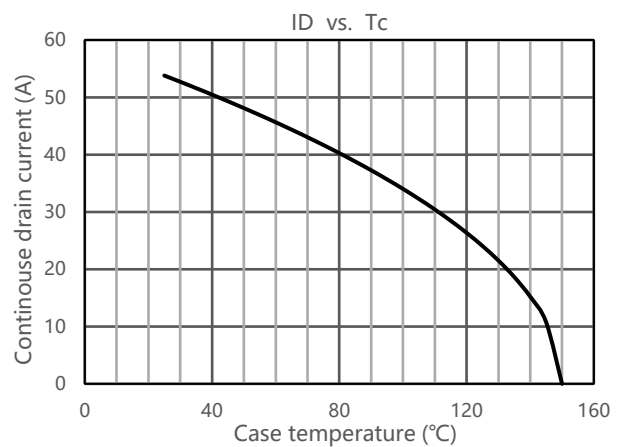


Figure 12. Maximum drain current vs. Case temperature



8 Test Circuit

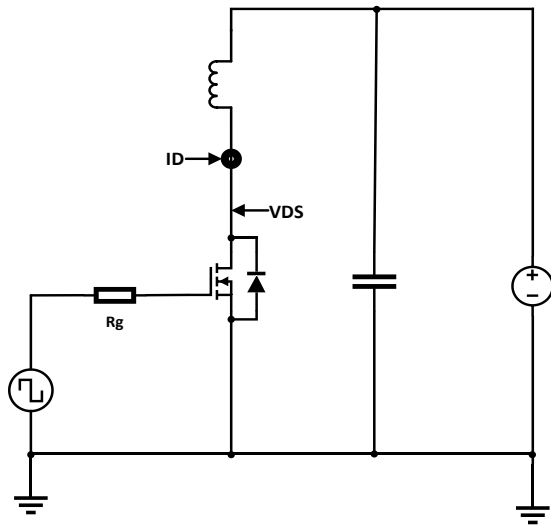
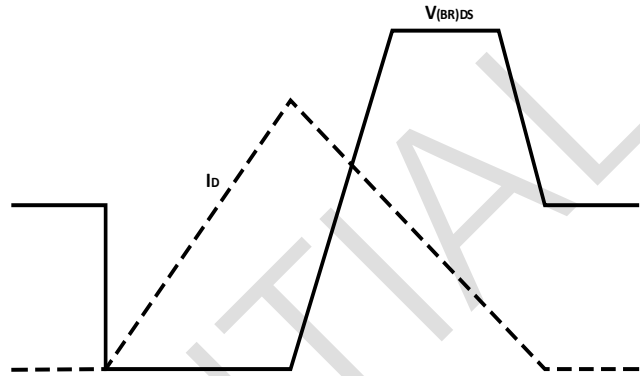


Figure 13. Unclamped inductive switching test circuit



Waveform 1. Unclamped inductive switching waveform

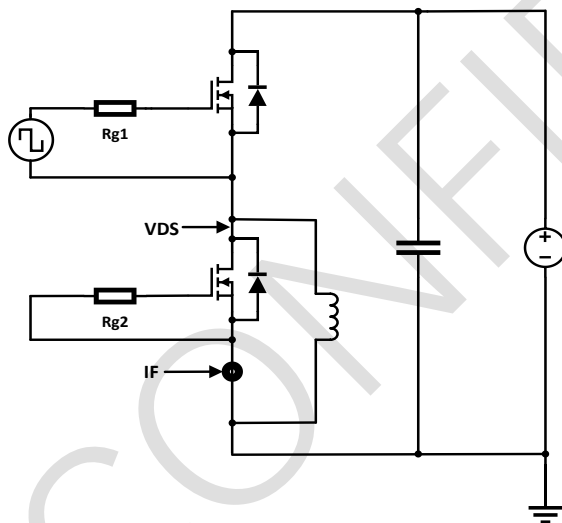
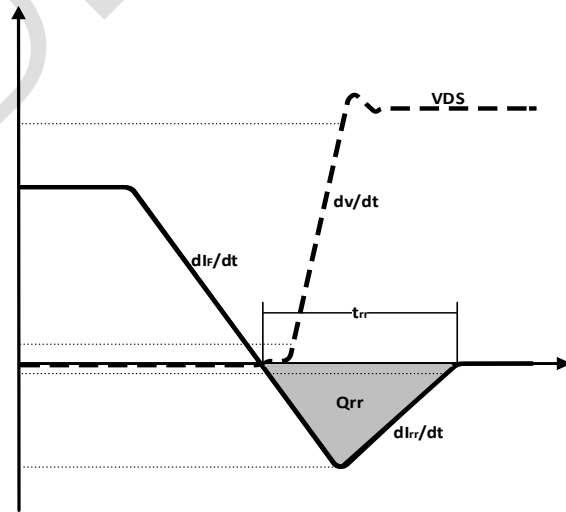


Figure 14. Body diode characteristics test circuit



Waveform 2. Body diode characteristics waveform

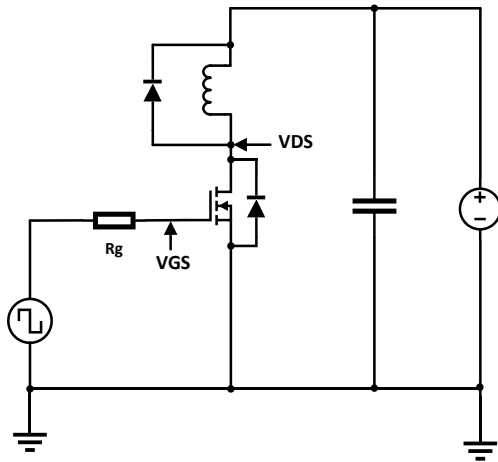
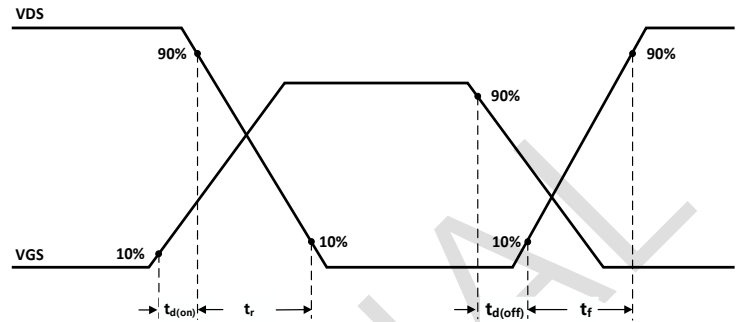
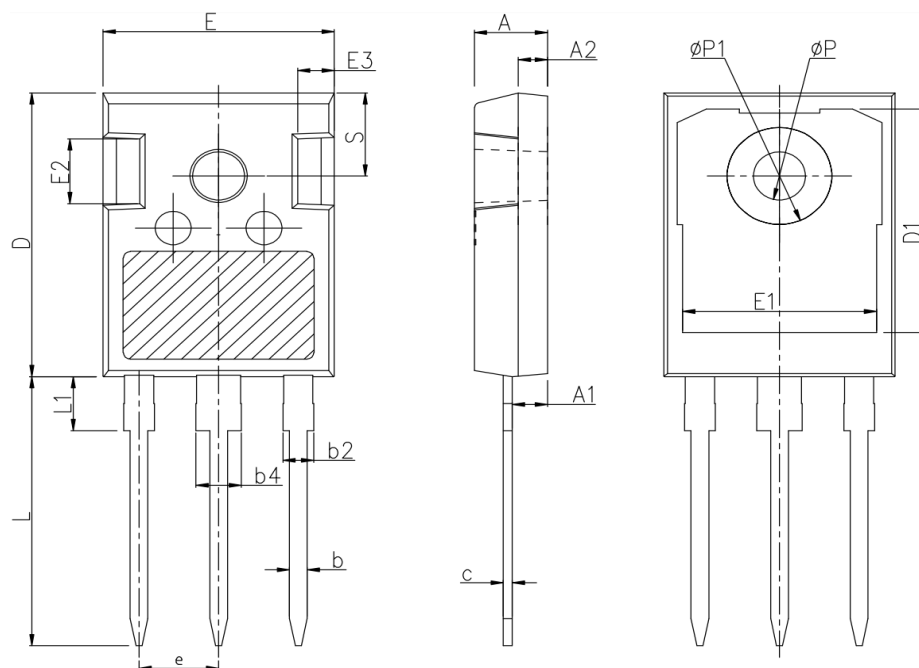


Figure 15. Switching time test circuit



Waveform 3. Switching time waveform

**PACKAGE INFORMATION**

SYMBOL	mm		
	MIN	NOM	MAX
A	4.80	5.00	5.20
A1	2.21	2.41	2.59
A2	1.85	2.00	2.15
b	1.11	1.21	1.36
b2	1.91	2.01	2.21
b4	2.91	3.01	3.21
c	0.51	0.61	0.75
D	20.80	21.00	21.30
D1	16.25	16.55	16.85
E	15.50	15.80	16.10
E1	13.00	13.30	13.60
E2	4.80	5.00	5.20
E3	2.30	2.50	2.70
e	5.44BSC		
L	19.82	19.92	20.22
L1	-	-	4.30
ϕP	3.40	3.60	3.80
$\phi P1$	-	-	7.30
S	6.15BSC		